



# STB8N65M5, STD8N65M5, STF8N65M5 STI8N65M5, STP8N65M5, STU8N65M5

N-channel 650 V, 0.56  $\Omega$ , 7 A MDmesh™ V Power MOSFET  
in D<sup>2</sup>PAK, I<sup>2</sup>PAK, TO-220, TO-220FP, DPAK and IPAK

## Features

Type	V <sub>DSS</sub> @ T <sub>Jmax</sub>	R <sub>DS(on)</sub> max.	I <sub>D</sub>
STB8N65M5	710 V	< 0.6 $\Omega$	7 A
STD8N65M5			
STF8N65M5			
STI8N65M5			
STP8N65M5			
STU8N65M5			

- Worldwide best R<sub>DS(on)</sub> \* area
- Higher V<sub>DSS</sub> rating
- High dv/dt capability
- Excellent switching performance
- Easy to drive
- 100% avalanche tested

## Application

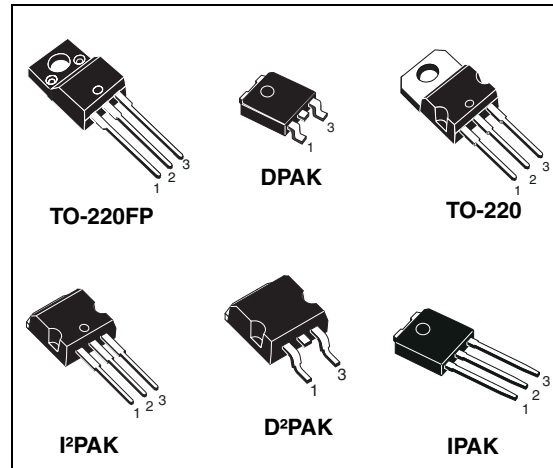
Switching applications

## Description

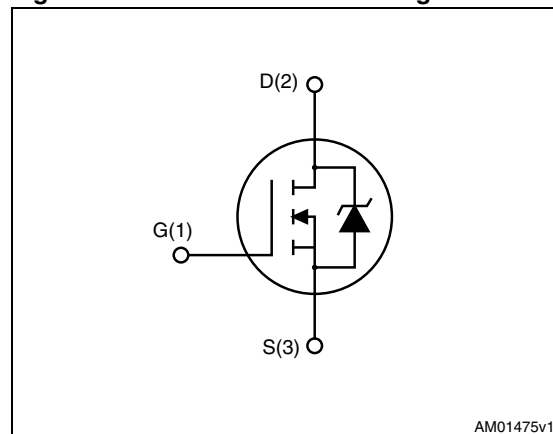
These devices are N-channel MDmesh™ V Power MOSFET based on an innovative proprietary vertical process technology, which is combined with STMicroelectronics' well-known PowerMESH™ horizontal layout structure. The resulting product has extremely low on-resistance, which is unmatched among silicon-based Power MOSFETs, making it especially suitable for applications which require superior power density and outstanding efficiency.

**Table 1. Device summary**

Order codes	Marking	Package	Packaging
STB8N65M5	8N65M5	D <sup>2</sup> PAK	Tape and reel
STD8N65M5		DPAK	Tape and reel
STF8N65M5		TO-220FP	Tube
STI8N65M5		I <sup>2</sup> PAK	Tube
STP8N65M5		TO-220	Tube
STU8N65M5		IPAK	Tube



**Figure 1. Internal schematic diagram**



AM01475v1

## Contents

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value			Unit
		TO-220, D <sup>2</sup> PAK I <sup>2</sup> PAK	IPAK DPAK,	TO-220FP	
V <sub>GS</sub>	Gate- source voltage	± 25			V
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 25 °C	7		7 <sup>(1)</sup>	A
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 100 °C	4.4		4.4 <sup>(1)</sup>	A
I <sub>DM</sub> <sup>(2)</sup>	Drain current (pulsed)	28		28 <sup>(1)</sup>	A
P <sub>TOT</sub>	Total dissipation at T <sub>C</sub> = 25 °C	70		25	W
I <sub>AR</sub>	Max current during repetitive or single pulse avalanche (pulse width limited by T <sub>JMAX</sub> )	2			A
E <sub>AS</sub>	Single pulse avalanche energy (starting T <sub>J</sub> = 25°C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 50V)	120			mJ
dv/dt <sup>(3)</sup>	Peak diode recovery voltage slope	15			V/ns
V <sub>ISO</sub>	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s; T <sub>C</sub> = 25 °C)			2500	V
T <sub>stg</sub>	Storage temperature	-55 to 150			°C
T <sub>j</sub>	Max. operating junction temperature	150			°C

- Limited only by maximum temperature allowed.
- Pulse width limited by safe operating area.
- I<sub>SD</sub> ≤ 7A, di/dt ≤ 400 A/μs, V<sub>Peak</sub> < V<sub>(BR)DSS</sub>.

**Table 3. Thermal data**

Symbol	Parameter	Value						Unit
		DPAK	IPAK	TO-220	I <sup>2</sup> PAK	D <sup>2</sup> PAK	TO-220FP	
R <sub>thj-case</sub>	Thermal resistance junction-case max	1.79					5	°C/W
R <sub>thj-amb</sub>	Thermal resistance junction-ambient max		100	62.5			62.5	°C/W
R <sub>thj-pcb</sub> <sup>(1)</sup>	Thermal resistance junction-pcb max	50				30		°C/W
T <sub>l</sub>	Maximum lead temperature for soldering purpose			300			300	°C

- When mounted on 1 inch<sup>2</sup> FR-4 board, 2oz Cu.

## 2 Electrical characteristics

( $T_C = 25\text{ °C}$  unless otherwise specified)

**Table 4. On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$ , $V_{GS} = 0$	650			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = \text{Max rating}$ $V_{DS} = \text{Max rating}$ , $T_C = 125\text{ °C}$			1 100	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate-body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 25\text{ V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$ , $I_D = 3.5\text{ A}$		0.56	0.6	$\Omega$

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 100\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0$	-	690	-	pF
$C_{oss}$	Output capacitance			18		pF
$C_{rss}$	Reverse transfer capacitance			2		pF
$C_{o(er)}^{(1)}$	Equivalent output capacitance energy related	$V_{GS} = 0$ , $V_{DS} = 0\text{ to }520\text{ V}$	-	17	-	pF
$C_{o(tr)}^{(2)}$	Equivalent output capacitance time related	$V_{GS} = 0$ , $V_{DS} = 0\text{ to }520\text{ V}$	-	52	-	pF
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	2.4	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 520\text{ V}$ , $I_D = 3.5\text{ A}$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 19</a> )	-	15	-	nC
$Q_{gs}$	Gate-source charge			3.6		nC
$Q_{gd}$	Gate-drain charge			6		nC

- $C_{o(er)}$  is a constant capacitance value that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$
- $C_{o(tr)}$  is a constant capacitance value that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off delay time	$V_{DD} = 400\text{ V}$ , $I_D = 4\text{ A}$ , $R_G = 4.7\ \Omega$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 20</a> ) (see <a href="#">Figure 23</a> )		50		ns
$t_{r(V)}$	Rise time		-	14	-	ns
$t_{c(off)}$	Cross time				20	ns
$t_{f(i)}$	Fall time				11	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		7	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				28	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 7\text{ A}$ , $V_{GS} = 0$	-		1.5	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 7\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ (see <a href="#">Figure 20</a> )	-	35		ns
$Q_{rr}$	Reverse recovery charge			268	nC	
$I_{RRM}$	Reverse recovery current			16	A	
$t_{rr}$	Reverse recovery time	$I_{SD} = 7\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$ (see <a href="#">Figure 20</a> )	-	103		ns
$Q_{rr}$	Reverse recovery charge			750	nC	
$I_{RRM}$	Reverse recovery current			15	A	

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220, I<sup>2</sup>PAK, D<sup>2</sup>PAK

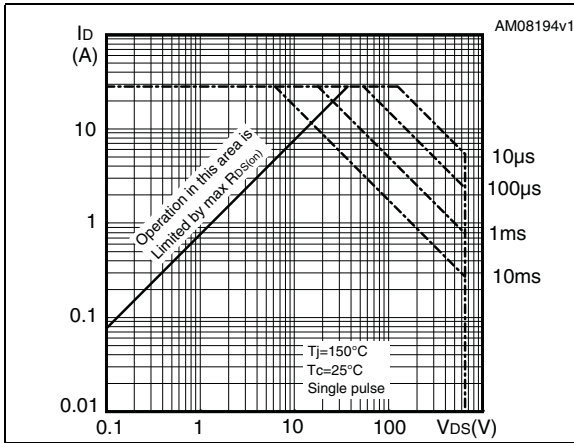


Figure 3. Thermal impedance for TO-220, I<sup>2</sup>PAK, D<sup>2</sup>PAK

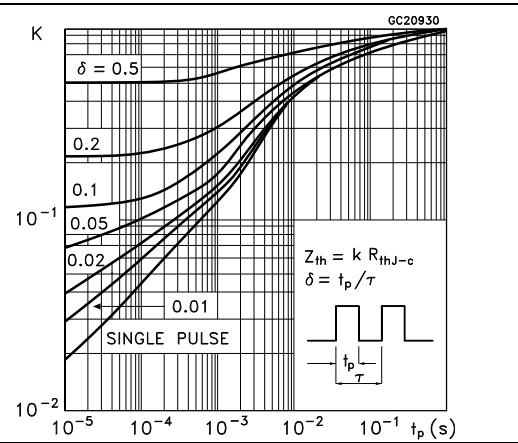


Figure 4. Safe operating area for DPAK, IPAK

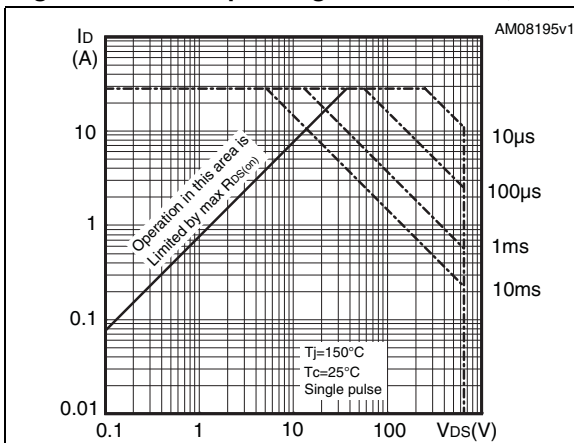


Figure 5. Thermal impedance for DPAK, IPAK

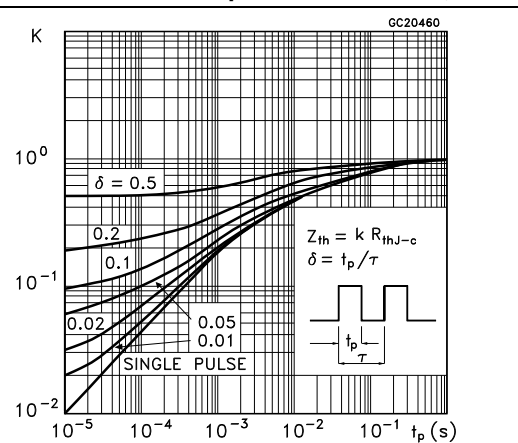


Figure 6. Safe operating area for TO-220FP

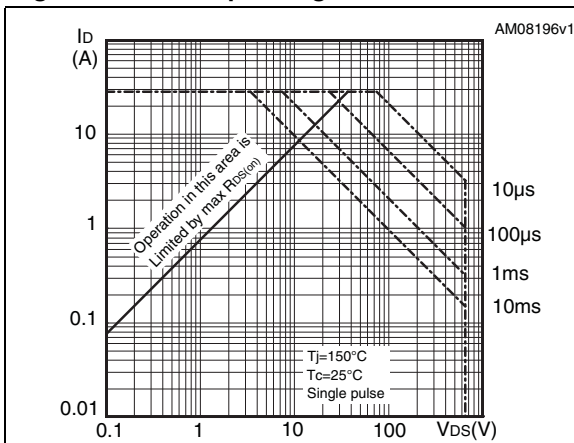


Figure 7. Thermal impedance for TO-220FP

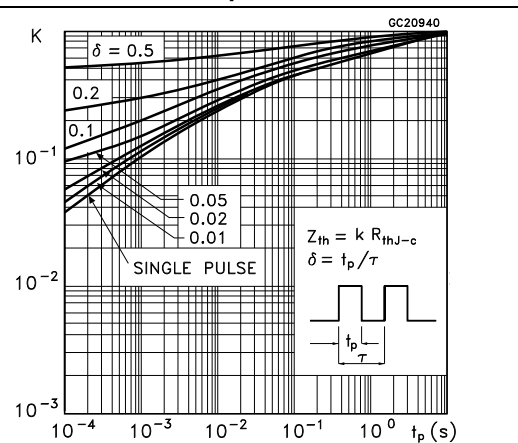


Figure 8. Output characteristics

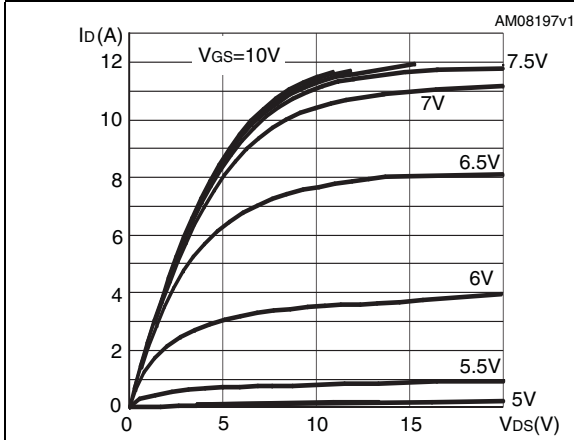


Figure 9. Transfer characteristics

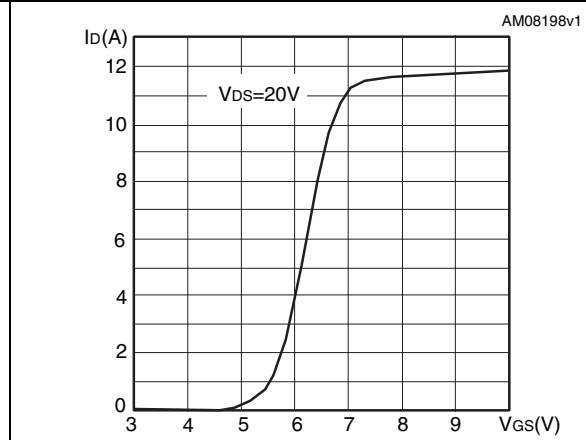


Figure 10. Gate charge vs gate-source voltage

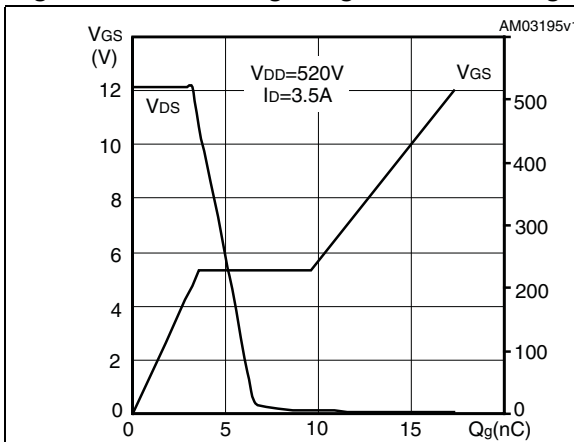


Figure 11. Static drain-source on resistance

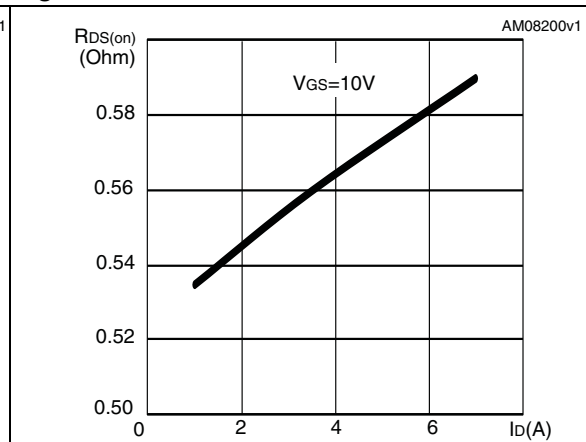


Figure 12. Capacitance variations

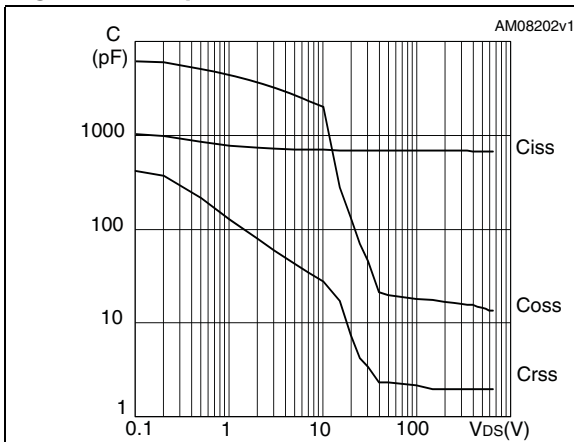


Figure 13. Output capacitance stored energy

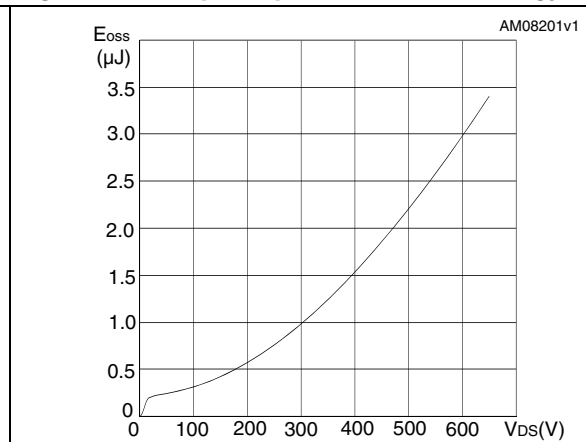


Figure 14. Normalized gate threshold voltage vs temperature

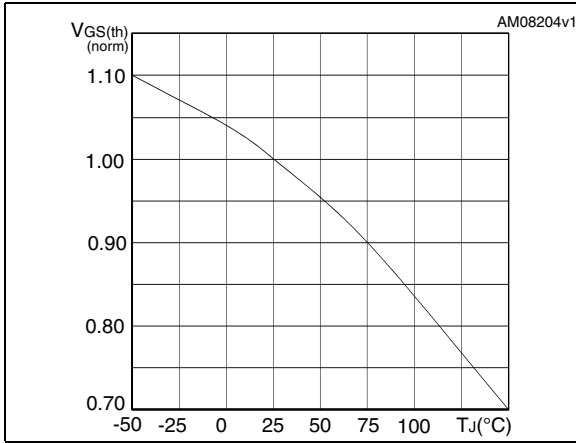


Figure 15. Normalized on resistance vs temperature

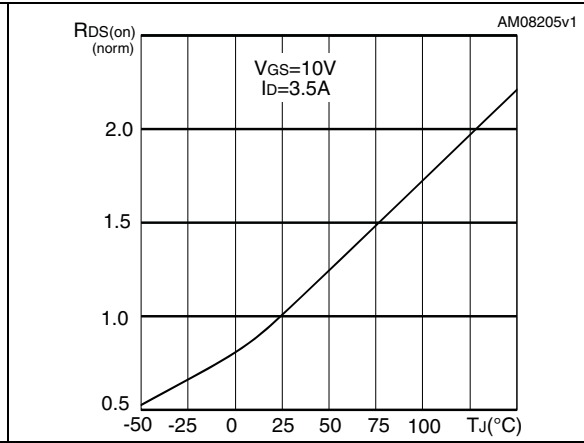


Figure 16. Switching losses vs gate resistance (1)

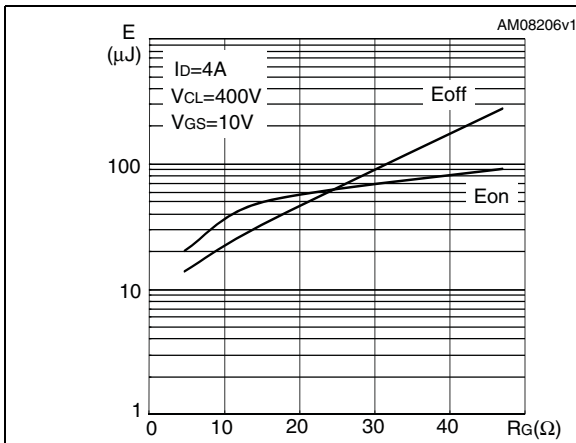
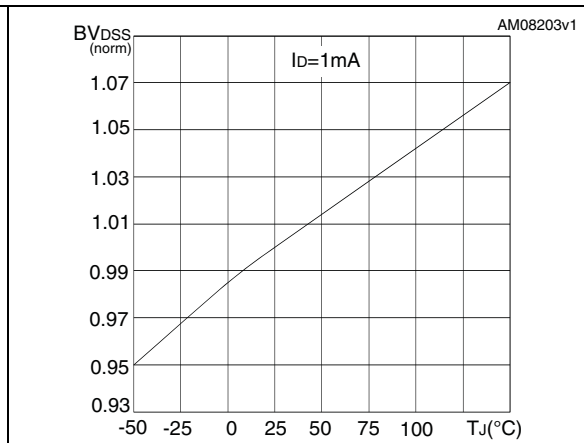


Figure 17. Normalized B<sub>V</sub>DSS vs temperature



1. Eon including reverse recovery of a SiC diode



### 3 Test circuits

Figure 18. Switching times test circuit for resistive load

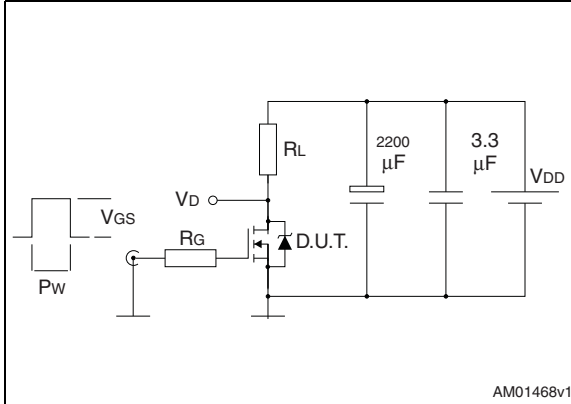


Figure 19. Gate charge test circuit

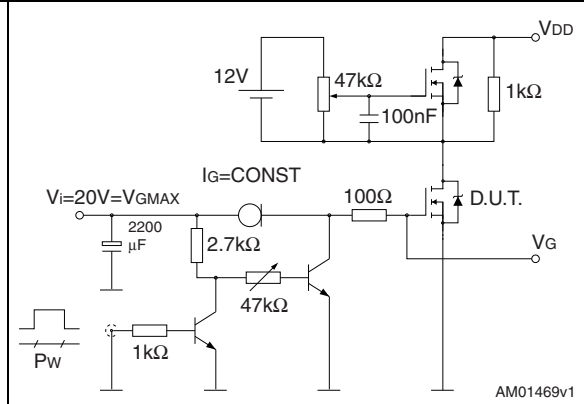


Figure 20. Test circuit for inductive load switching and diode recovery times

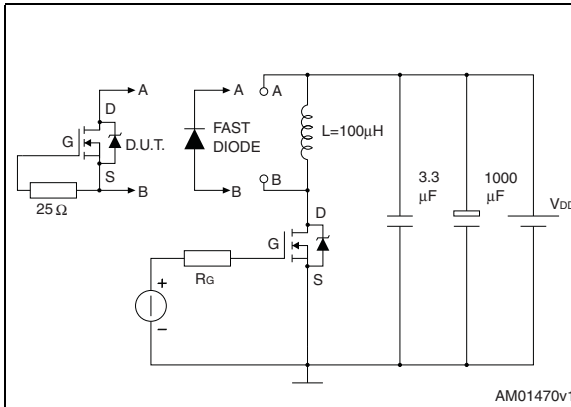


Figure 21. Unclamped inductive load test circuit

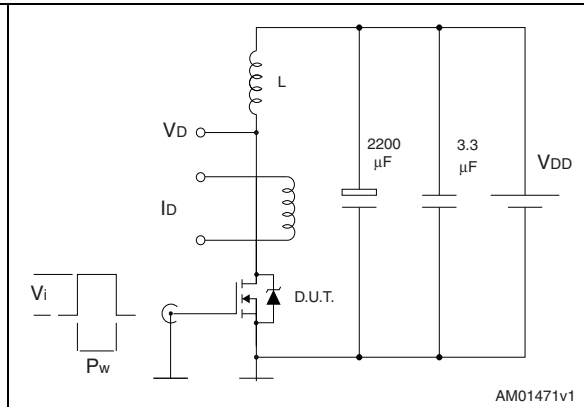


Figure 22. Unclamped inductive waveform

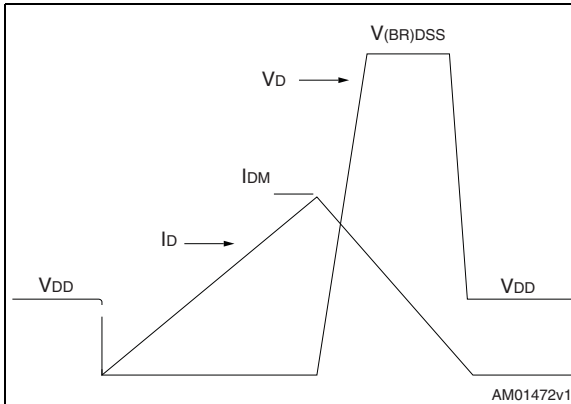
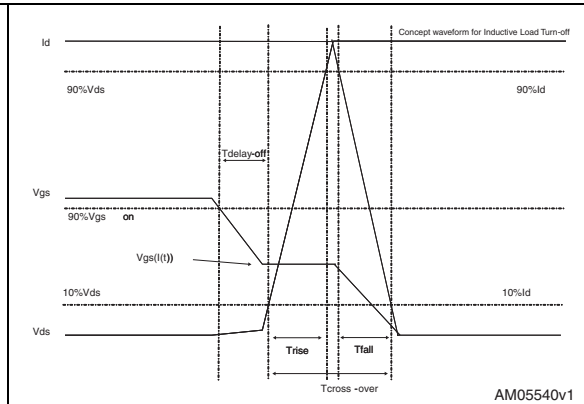


Figure 23. Switching time waveform



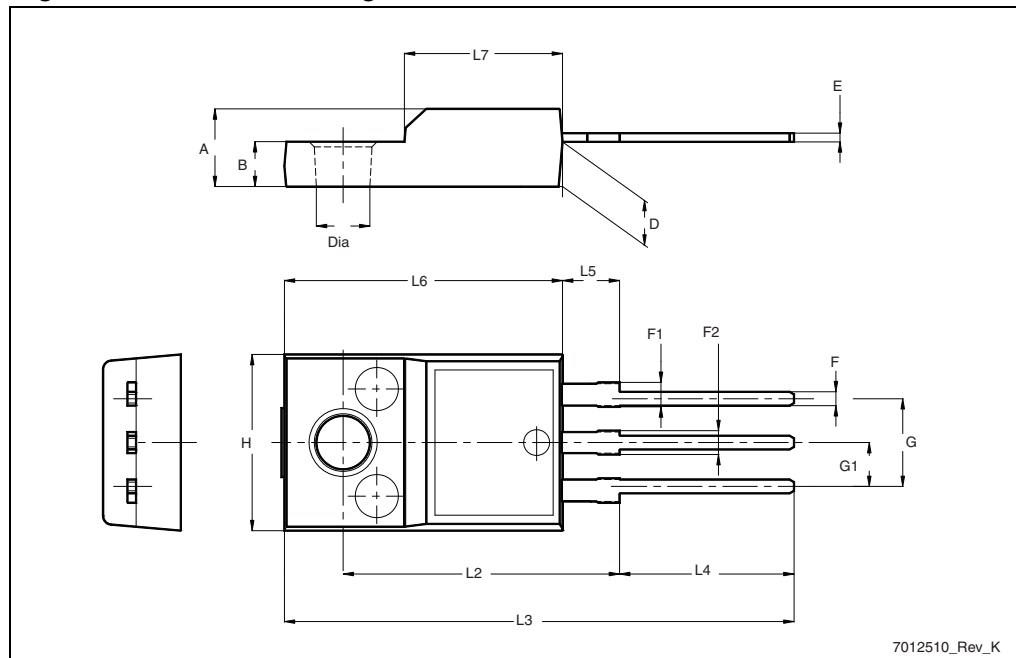
## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

Table 8. TO-220FP mechanical data

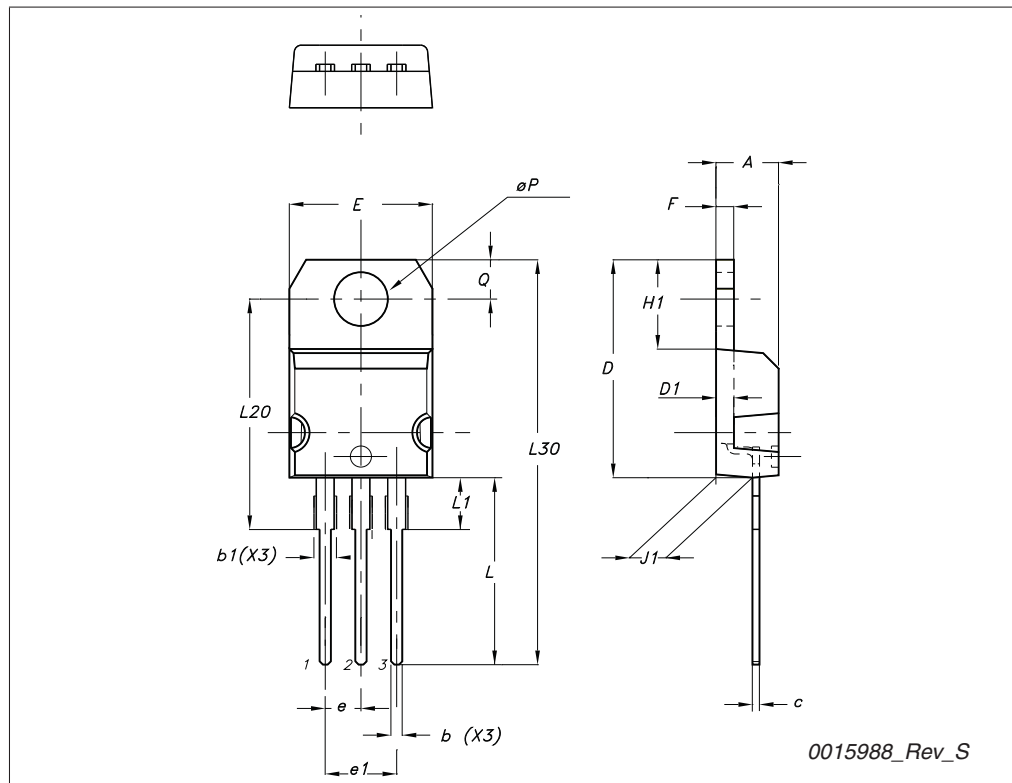
Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 24. TO-220FP drawing mechanical data



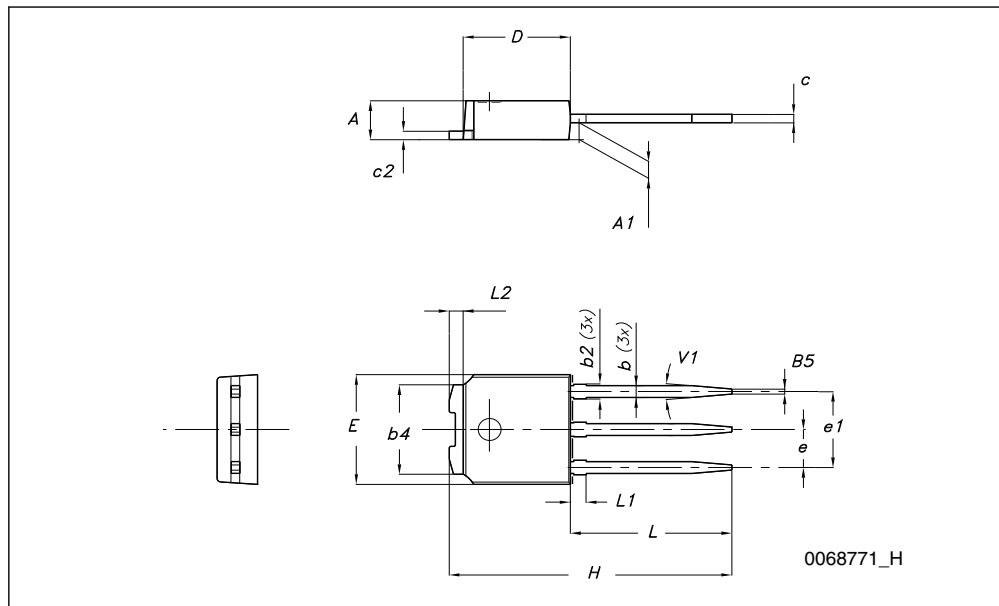
TO-220 type A mechanical data

Dim	mm		
	Min	Typ	Max
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
∅P	3.75		3.85
Q	2.65		2.95



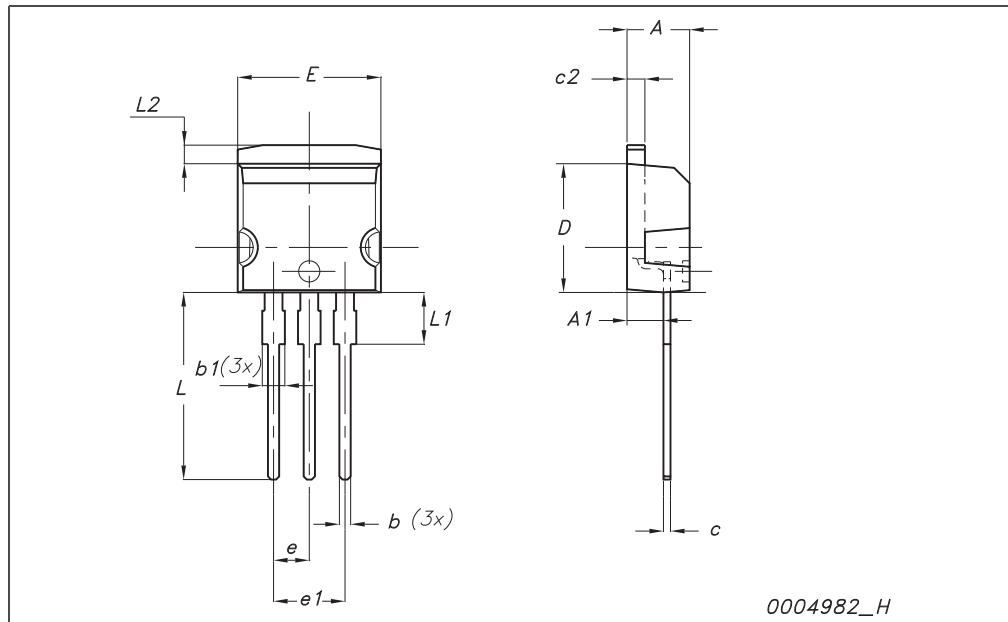
**TO-251 (IPAK) mechanical data**

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
(L1)	0.80		1.20
L2		0.80	
V1		10°	



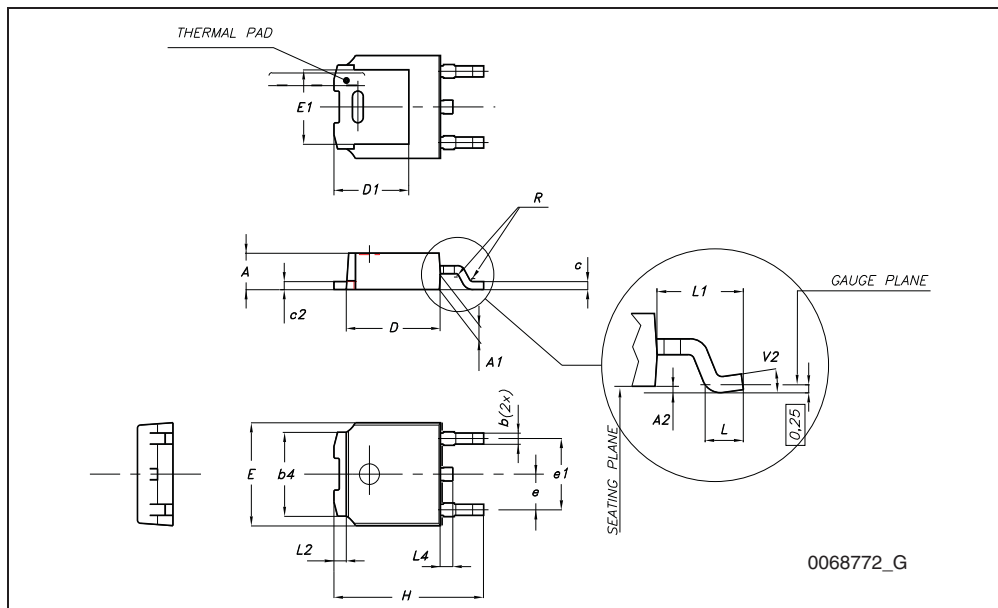
I<sup>2</sup>PAK (TO-262) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



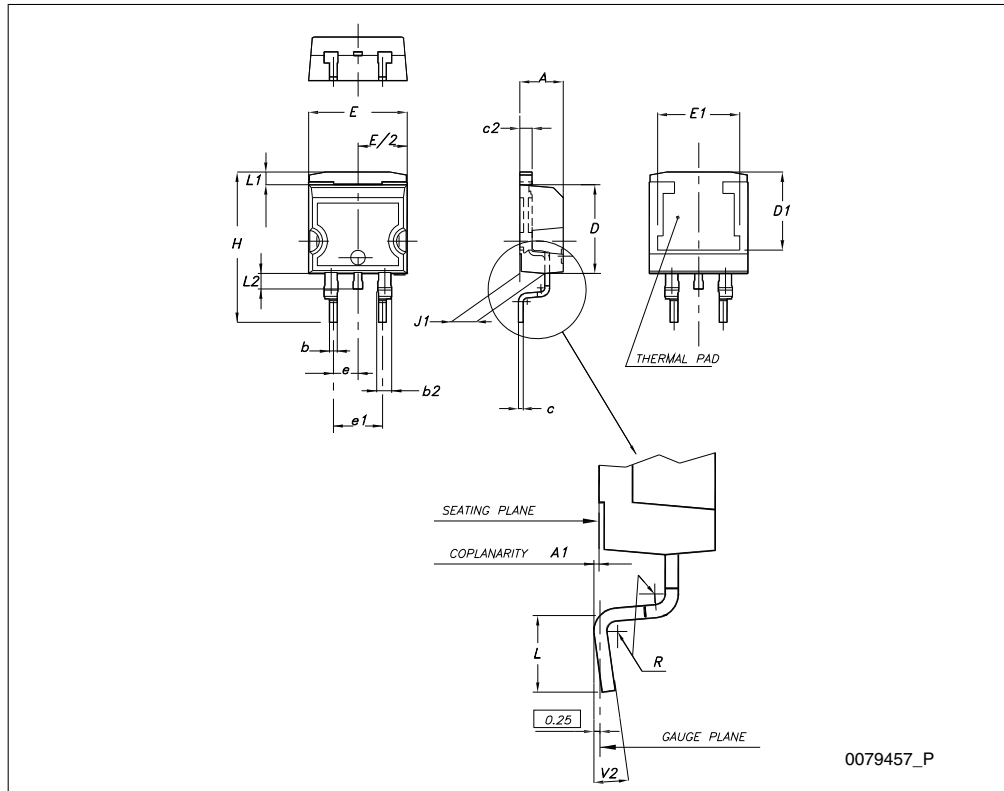
TO-252 (DPAK) mechanical data

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°



**D<sup>2</sup>PAK (TO-263) mechanical data**

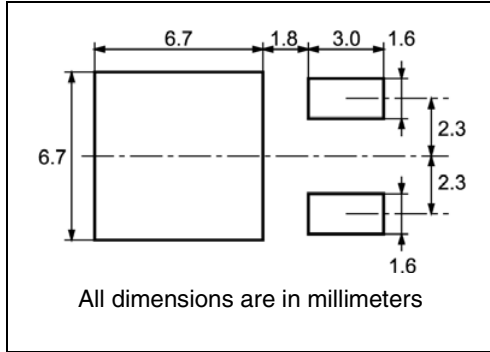
Dim.	mm.		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°





## 5 Packaging mechanical data

### DPAK FOOTPRINT



### TAPE AND REEL SHIPMENT

40 mm min. Access hole at slot location

Full radius

Tape slot in core for tape start 2.5mm min. width

G measured at hub

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	16.4	18.4	0.645	0.724
N	50		1.968	
T		22.4		0.881

BASE QTY	BULK QTY
2500	2500

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	6.8	7	0.267	0.275
B0	10.4	10.6	0.409	0.417
B1		12.1		0.476
D	1.5	1.6	0.059	0.063
D1	1.5		0.059	
E	1.65	1.85	0.065	0.073
F	7.4	7.6	0.291	0.299
K0	2.55	2.75	0.100	0.108
P0	3.9	4.1	0.153	0.161
P1	7.9	8.1	0.311	0.319
P2	1.9	2.1	0.075	0.082
R	40		1.574	
W	15.7	16.3	0.618	0.641

10 pitches cumulative tolerance on tape +/- 0.2 mm

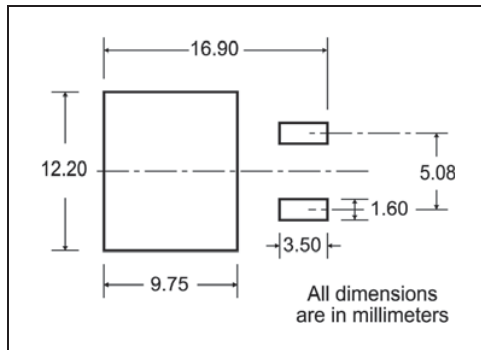
For machine ref. only including draft and radii concentric around B0

TRL

FEED DIRECTION

Bending radius R min.

D<sup>2</sup>PAK FOOTPRINT



TAPE AND REEL SHIPMENT

40 mm min. Access hole at slot location

Full radius

Tape slot in core for tape start 2.5mm min. width

G measured at hub

REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

10 pitches cumulative tolerance on tape +/- 0.2 mm

Center line of cavity

User Direction of Feed

FEED DIRECTION

Bending radius

## 6 Revision history

Table 9. Document revision history

Date	Revision	Changes
23-Oct-2009	1	First release
14-Oct-2010	2	Document status promoted from preliminary data to datasheet.

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